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SEMICONDUCTOR TM

KSE340

High Voltage General Purpose Applications

- High Collector-Emitter Breakdown Voltage
- Suitable for Transformer
- Complement to KSE350



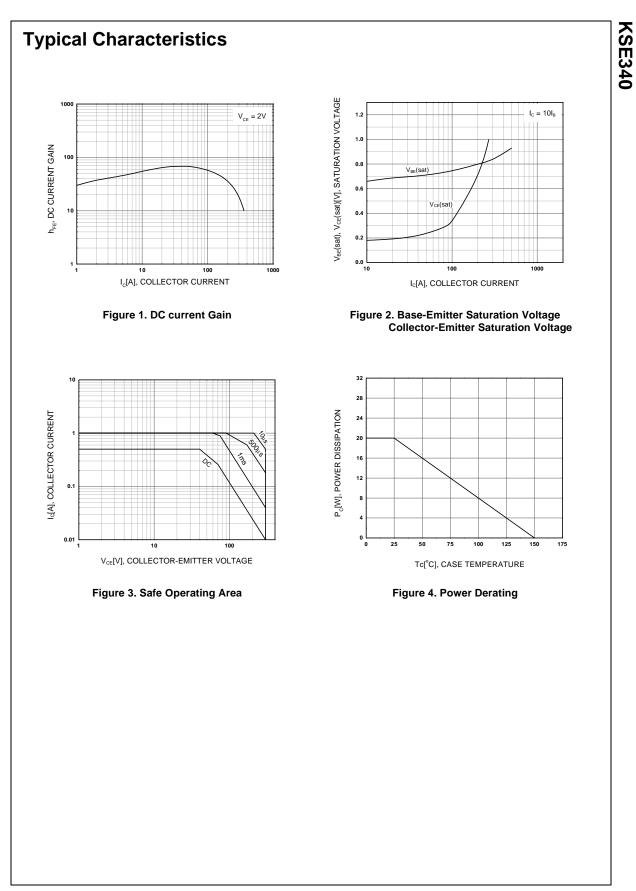
NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_{C}=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	300	V
V _{CEO}	Collector-Emitter Voltage	300	V
V _{EBO}	Emitter-Base Voltage	5	V
l _C	Collector Current	500	mA
Pc	Collector Dissipation (T _C =25°C)	20	W
Т _Ј	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 65 ~ 150	°C

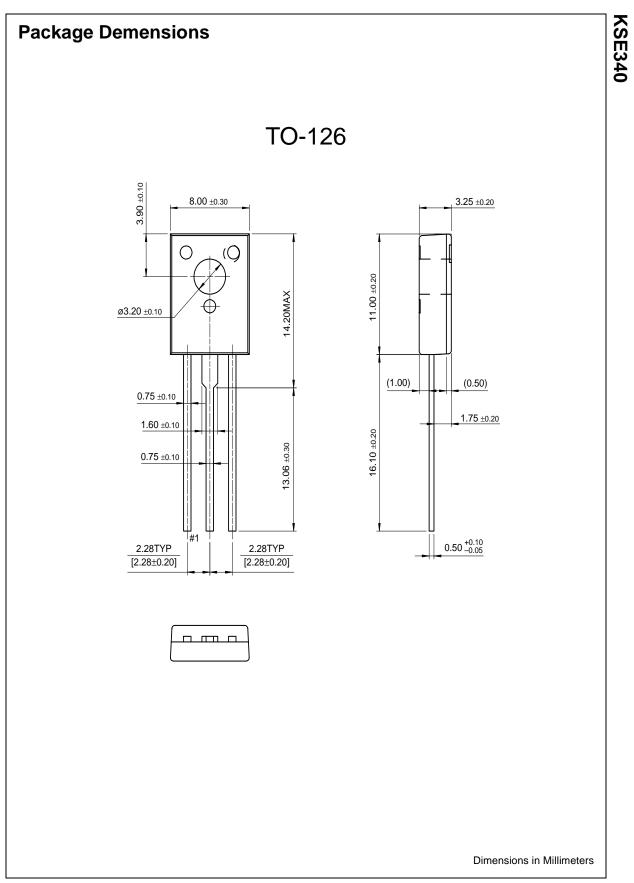
Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 1 {\rm mA}, I_{\rm B} = 0$	300		V
I _{CBO}	Collector Cut-off Current	V _{CB} = 300V, I _E =0		100	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{BE} = 3V, I_{C} = 0$		100	μΑ
h _{FE}	DC Current Gain	$V_{CE} = 10V, I_{C} = 50mA$	30	240	



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